## COMBINED DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled **DIELECTRIC LAYER FOR SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME**, the specification of which:

	[X]	is attached heret				
	[]	was filed on	8	as Application No		
	ΓÌ	and was amende	ed on	(if applicable)		
	ĹĴ	with amendment	ts through _	(if applicable).		
I he specificatio	reby state n, includi	that I have reviewing the claims, as a	ved and und amended by	erstand the contents of the aborany amendment referred to al	ove-iden bove.	tified
I ac this applica	knowledg tion in ac	ge the duty to discled	ose informa le 37, Code	ation which is material to the post of Federal Regulations, Sec. 1	oatentabi 1.56.	ility of
(a)-(d) or § of any PCT United State for patent of	365(b) of internation internat	any foreign appliconal application werica, listed below	cation(s) for which design and have a of any PCT	der Title 35, United States Coor patent or inventor's certificate at least one country other lso identified below any foreign international application having claimed:	te, or §30 r than th gn applio	65(a) e cation
Prior Forei	gn Applic	eation(s)			Clain Priori [ ]	-
(Number)		(Country)		(Day/Month/Year Filed)	Yes	No
		m the benefit unde		United States Code, Sec. 119(e	e) of any	' United
Provisional Application No. Filin					<u>ate</u>	
any PCT in insofar as	nternation the subject	al application desi	ignating the f the claims	United States Code, Sec. 120 of United States of America list of this application is not disclaided by the first paragraph of	ed below losed in t	v and, the

United States Code, Sec. 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Sec. 1.56 which occurred

between the filing date of the prior application and the national or PCT international filing date of this application:

(Application No.) (Filing Date) (Status) (patented, pending, abandoned)

I hereby appoint the following attorneys to prosecute the application, to file a corresponding international application, to prosecute and transact all business in the Patent and Trademark Office connected therewith:

Customer No. 20575

Attorney Name	Registration No.
Jerome S. Marger Alexander C. Johnson, Jr.	26,480 29,396
Alan T. McCollom	28,881
James G. Stewart	32,496 34,555
Glenn C. Brown Stephen S. Ford	35,139
Gregory T. Kavounas	37,862
Scott A. Schaffer Joseph S. Makuch	38,610 39,286
James E. Harris	40,013
Graciela G. Cowger	42,444 43 <b>,</b> 054
Ariel Rogson Craig R. Rogers	43,888

Direct all telephone calls to at (503) 222-3613 and send all correspondence to:

MARGER JOHNSON & McCOLLOM, P.C. 1030 S.W. Morrison Street Portland, Oregon 97205

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Full name of sole or fit	st inventor: Jongho LEE	
Inventor's signature: _	Lee porgho	Feb. 1 2001' (Date)
Residence: Korea		

Residence: Korea

Citizenship: Korea

Post Office address: 103-308 Doo-jin Apt., Youngduck-Ri Kiheung-Eup youngin-City, Kyunggi-Do

Korea

Full name of sole or first inventor: Nae-In LEE

Inventor's signature: Nae In Lee Feb. 1, 2001
(Date)

Residence: Korea

Citizenship: Korea

Post Office address: 116-401 Kwan-ak Hyun Dai Apt.

Bong-chun 3 dong, kwan-Ak Gu

Seoul, Korea